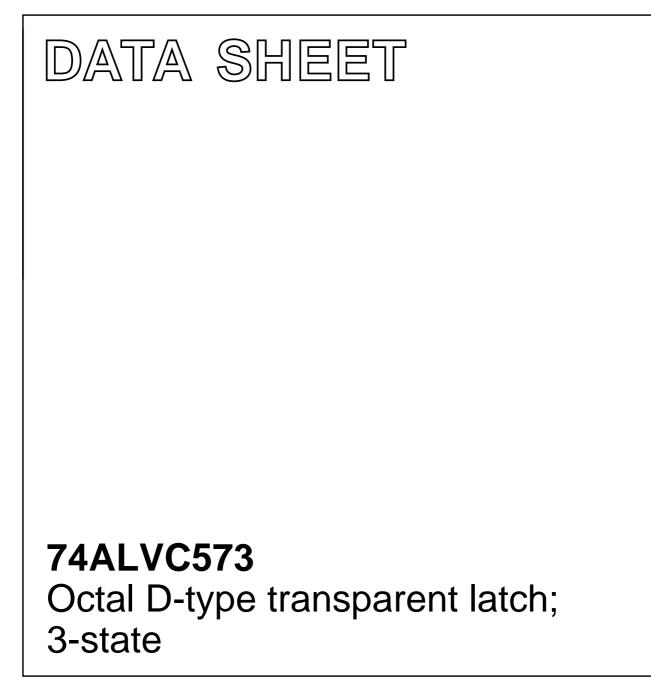
INTEGRATED CIRCUITS



Product specification Supersedes data of 2002 Mar 01 2003 Jun 25



### 74ALVC573

#### FEATURES

- Wide supply voltage range from 1.65 to 3.6 V
- Complies with JEDEC standards: JESD8-7 (1.65 to 1.95 V) JESD8-5 (2.3 to 2.7 V) JESD8B/JESD36 (2.7 to 3.6 V).
- 3.6 V tolerant inputs and outputs
- CMOS low power consumption
- Direct interface with TTL levels (2.7 to 3.6 V)
- Power-down mode
- Latch-up performance exceeds 250 mA
- ESD protection: HBM EIA/JESD22-A114-A exceeds 2000 V MM EIA/JESD22-A115-A exceeds 200 V.

#### DESCRIPTION

The 74ALVC573 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families. The 74ALVC573 is an octal D-type transparent latch featuring separate D-type inputs for each latch and 3-state outputs for bus oriented applications. A latch enable (LE) input and an output enable  $(\overline{OE})$  input are common to all internal latches.

The 74ALVC573 consists of eight D-type transparent latches with 3-state true outputs. When LE is HIGH, data at the Dn inputs enters the latches. In this condition the latches are transparent, i.e. a latch output will change state each time its corresponding D-input changes.

When LE is LOW the latches store the information that was present at the D-inputs a set-up time preceding the HIGH-to-LOW transition of LE. When  $\overline{OE}$  is LOW, the contents of the 8 latches are available at the outputs. When  $\overline{OE}$  is HIGH, the outputs go to the high-impedance OFF-state. Operation of the  $\overline{OE}$  input does not affect the state of the latches.

The 74ALVC573 is functionally identical to the 74ALVC373, but the has a different pin arrangement.

### 

GND = 0 V;  $T_{amb}$  = 25 °C.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay input Dn to output Qn	$V_{CC}$ = 1.8 V; $C_L$ = 30 pF; $R_L$ = 1 k $\Omega$	2.5	ns
		$V_{CC} = 2.5 \text{ V}; \text{ C}_{L} = 30 \text{ pF}; \text{ R}_{L} = 500 \Omega$	2.0	ns
		$V_{CC} = 2.7 \text{ V}; \text{ C}_{L} = 50 \text{ pF}; \text{ R}_{L} = 500 \Omega$	2.3	ns
		$V_{CC} = 3.3 \text{ V}; \text{ C}_{L} = 50 \text{ pF}; \text{ R}_{L} = 500 \Omega$	2.2	ns
CI	input capacitance		3.5	pF
C <sub>PD</sub>	power dissipation capacitance per buffer	V <sub>CC</sub> = 3.3 V; notes and 1		
		outputs enabled	37	pF
		outputs disabled	7	pF

#### Notes

 $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts;

N = total load switching outputs;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

1. The condition is  $V_I = GND$  to  $V_{CC}$ .

### 74ALVC573

### FUNCTION TABLE

See note 1

	INPUT	INTERNAL	OUTPUT	
ŌĒ	LE	Dn	LATCH	Qn
L	Н	L	L	L
L	Н	Н	Н	Н
L	L	I	L	L
L	L	h	Н	Н
Н	L	I	L	Z
Н	L	h	Н	Z
	L L L L H	OE LE   L H   L H   L L   L L   L L   L L   L L   L L	OE LE Dn   L H L   L H H   L L I   L L I   H L I   L L I   L L I   H L I	OELEDnLATCHLHLLLHHHLLILLLILLLILLLNHHLIL

#### Note

- 1. H = HIGH voltage level;
  - a) h = HIGH voltage level one set-up time prior to the HIGH-to-LOW LE transition;
  - b) L = LOW voltage level;
  - c) I = LOW voltage level one set-up time prior to the HIGH-to-LOW LE transition;
  - d) Z = high-impedance OFF-state.

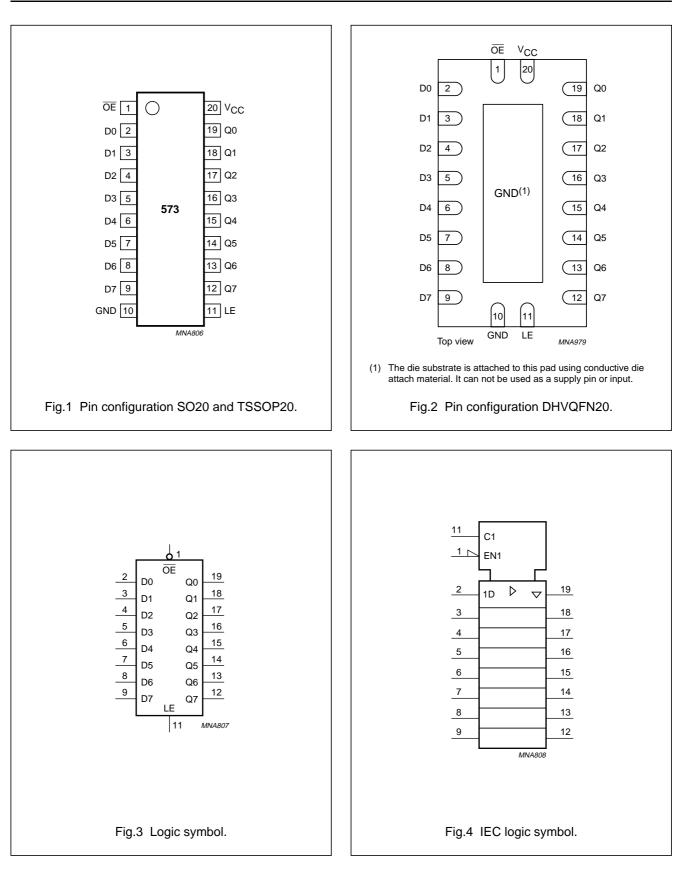
#### ORDERING INFORMATION

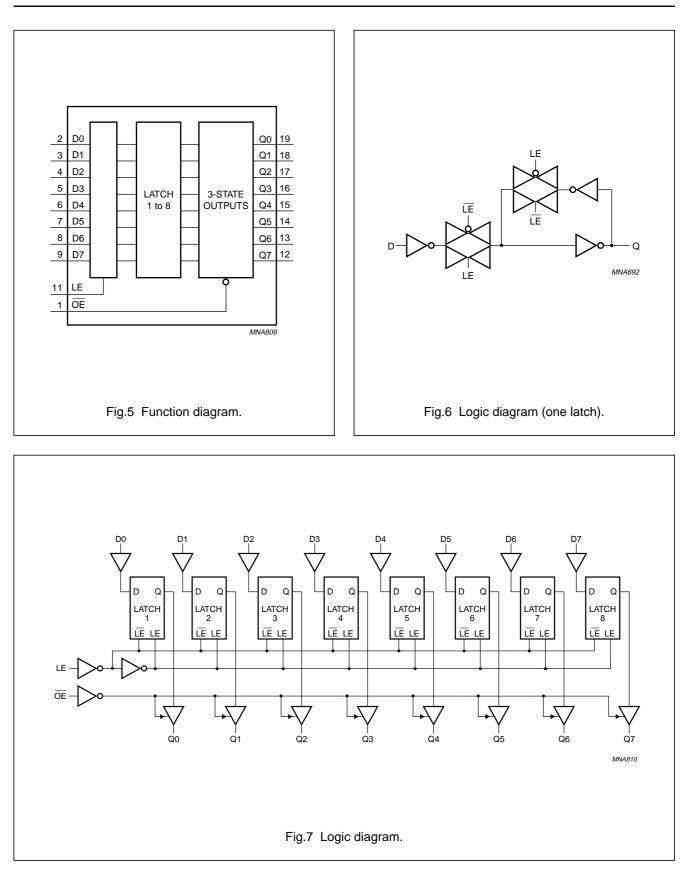
	PACKAGE							
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE			
74ALVC573D	–40 to +85 °C	20	SO20	plastic	SOT163-1			
74ALVC573PW	–40 to +85 °C	20	TSSOP20	plastic	SOT360-1			
74ALVC573BQ	–40 to +85 °C	20	DHVQFN20	plastic	SOT764-1			

#### PINNING

PIN	SYMBOL	DESCRIPTION
1	ŌĒ	output enable input (active LOW)
2	D0	data input
3	D1	data input
4	D2	data input
5	D3	data input
6	D4	data input
7	D5	data input
8	D6	data input
9	D7	data input
10	GND	ground (0 V)

PIN	SYMBOL	DESCRIPTION
11	LE	latch enable input (active HIGH)
12	Q7	3-state latch output
13	Q6	3-state latch output
14	Q5	3-state latch output
15	Q4	3-state latch output
16	Q3	3-state latch output
17	Q2	3-state latch output
18	Q1	3-state latch output
19	Q0	3-state latch output
20	V <sub>CC</sub>	supply voltage





### 74ALVC573

#### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		1.65	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	$V_{CC}$ = 1.65 to 3.6 V; enable mode	0	V <sub>CC</sub>	V
		$V_{CC}$ = 1.65 to 3.6 V; disable mode	0	3.6	V
		V <sub>CC</sub> = 0 V; Power-down mode	0	3.6	V
T <sub>amb</sub>	operating ambient temperature		-40	+85	°C
t <sub>r</sub> , t <sub>f</sub>	input rise and fall times	$V_{CC}$ = 1.65 to 2.7 V	0	20	ns/V
		V <sub>CC</sub> = 2.7 to 3.6 V	0	10	ns/V

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input diode current	V <sub>1</sub> < 0	_	-50	mA
VI	input voltage		-0.5	+4.6	V
I <sub>OK</sub>	output diode current	$V_{\rm O} > V_{\rm CC}$ or $V_{\rm O} < 0$	-	±50	mA
Vo	output voltage	enable mode; notes 1 and 2	-0.5	V <sub>CC</sub> + 0.5	V
		disable mode	-0.5	+4.6	V
		Power-down mode; note 2	-0.5	+4.6	V
lo	output source or sink current	$V_{O} = 0$ to $V_{CC}$	_	±50	mA
I <sub>CC</sub> , I <sub>GND</sub>	V <sub>CC</sub> or GND current		-	±100	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	power dissipation	$T_{amb} = -40$ to +85 °C; note 3	_	500	mW

#### Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. When  $V_{CC} = 0 V$  (Power-down mode), the output voltage can be 3.6 V in normal operation.
- 3. For SO20 packages: above 70 °C the value of  $P_{tot}$  derates linearly with 8 mW/K.
  - a) For TSSOP20 packages: above 60 °C the value of P<sub>tot</sub> derates linearly with 5.5 mW/K.
  - b) For DHVQFN20 packages: above 60 °C the value of P<sub>tot</sub> derates linearly with 4.5 mW/K.

### 74ALVC573

#### DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL		TEST CONDI		<b>TVD</b> (1)			
SYMBOL	PARAMETER	OTHER	V <sub>CC</sub> (V)	– MIN.	<b>TYP.</b> <sup>(1)</sup>	MAX.	UNIT
T <sub>amb</sub> = -40	) to +85°C	1		•	•		
V <sub>IH</sub>	HIGH-level input		1.65 to 1.95	$0.65 \times V_{CC}$	-	-	V
	voltage		2.3 to 2.7	1.7	-	_	V
			2.7 to 3.6	2	-	_	V
V <sub>IL</sub>	LOW-level input		1.65 to 1.95	-	-	$0.35 \times V_{CC}$	V
	voltage		2.3 to 2.7	-	-	0.7	V
			2.7 to 3.6	-	-	0.8	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	I <sub>O</sub> = 100 μA	1.65 to 3.6	-	-	0.2	V
		l <sub>O</sub> = 6 mA	1.65	-	-	0.3	V
		l <sub>O</sub> = 12 mA	2.3	-	-	0.4	V
		l <sub>O</sub> = 18 mA	2.3	-	-	0.6	V
		l <sub>O</sub> = 12 mA	2.7	-	-	0.4	V
		l <sub>O</sub> = 18 mA	3.0	-	-	0.4	V
		I <sub>O</sub> = 24 mA	3.0	-	-	0.55	V
V <sub>OH</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	I <sub>O</sub> = -100 μA	1.65 to 3.6	V <sub>CC</sub> – 0.2	-	-	V
		I <sub>O</sub> = -6 mA	1.65	1.25	-	-	V
		I <sub>O</sub> = -12 mA	2.3	1.8	-	-	V
		I <sub>O</sub> = -18 mA	2.3	1.7	-	-	V
		I <sub>O</sub> = -12 mA	2.7	2.2	-	-	V
		I <sub>O</sub> = -18 mA	3.0	2.4	-	-	V
		I <sub>O</sub> = -24 mA	3.0	2.2	-	-	V
ILI	input leakage current	$V_{I} = 3.6 \text{ V or GND}$	3.6	-	±0.1	±5	μA
I <sub>OZ</sub>	3-state output OFF-state current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = 3.6 \text{ V or GND};$ note 2	1.65 to 3.6	-	0.1	±10	μA
l <sub>off</sub>	power OFF leakage current	$V_{\rm I}$ or $V_{\rm O}$ = 0 to 3.6 V	0.0	-	±0.1	±10	μA
I <sub>CC</sub>	quiescent supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$	3.6	-	0.2	10	μA
ΔI <sub>CC</sub>	additional quiescent supply current per input pin	$V_{I} = V_{CC} - 0.6 V;$ $I_{O} = 0$	3.0 to 3.6	-	5	750	μA

#### Notes

1. All typical values are measured at V\_{CC} = 3.3 V and T\_{amb} = 25 °C.

2. For transceivers, the parameter  $I_{\mbox{\scriptsize OZ}}$  includes the input leakage current.

### 74ALVC573

#### AC CHARACTERISTICS

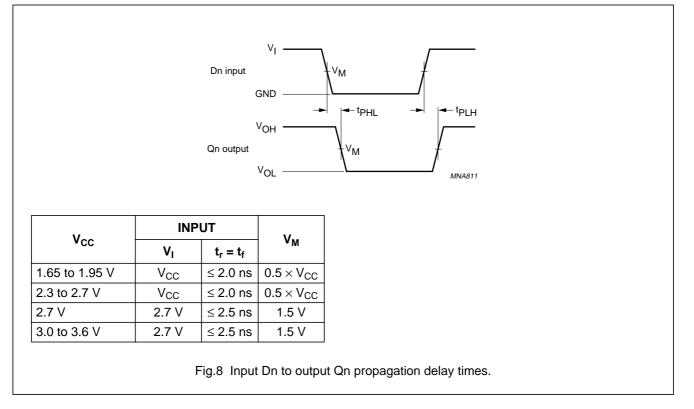
		TEST COND	ITIONS		TVD		
SYMBOL PARAMETER		WAVEFORMS	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	
T <sub>amb</sub> = -40	) to +85 °C; see note 1		•		•	_	-1
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay Dn to Qn	see Figs 8 and 12	1.65 to 1.95	1.0	2.5	5.4	ns
		_	2.3 to 2.7	1.0	2.0	3.5	ns
			2.7	1.0	2.3	3.6	ns
			3.0 to 3.6	1.0	2.2	3.3	ns
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay LE to Qn	see Figs 9 and 12	1.65 to 1.95	1.0	2.8	6.0	ns
			2.3 to 2.7	1.0	2.1	3.8	ns
			2.7	1.0	2.4	3.7	ns
		3.0 to 3.6	1.0	2.3	3.3	ns	
t <sub>PZH</sub> /t <sub>PZL</sub>	3-state output enable time	see Figs 10 and 12	1.65 to 1.95	1.5	3.0	6.4	ns
	OE to Qn		2.3 to 2.7	1.0	2.4	4.5	ns
			2.7	1.5	3.0	4.6	ns
		3.0 to 3.6	1.0	2.3	4.0	ns	
t <sub>PHZ</sub> /t <sub>PLZ</sub>	3-state output disable time	see Figs 10 and 12	1.65 to 1.95	1.5	3.4	7.0	ns
	OE to Qn		2.3 to 2.7	1.0	2.2	4.4	ns
			2.7	1.5	2.8	4.4	ns
			3.0 to 3.6	1.0	2.7	4.4	ns
t <sub>W</sub>	LE pulse with HIGH	see Figs 9 and 12	1.65 to 1.95	3.8	-	_	ns
		_	2.3 to 2.7	3.3	-	_	ns
			2.7	3.3	-	_	ns
			3.0 to 3.6	3.3	-	_	ns
t <sub>su</sub>	set-up time Dn to LE	see Figs 11 and 12	1.65 to 1.95	0.8	-	_	ns
			2.3 to 2.7	0.8	-	_	ns
			2.7	0.8	-	_	ns
			3.0 to 3.6	0.8	-	_	ns
t <sub>h</sub>	hold time Dn to LE	see Figs 11 and 12	1.65 to 1.95	0.8	-	_	ns
			2.3 to 2.7	0.8	-	_	ns
			2.7	0.8	-	_	ns
			3.0 to 3.6	0.7	_	_	ns

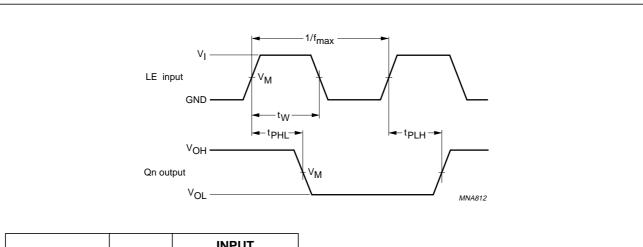
#### Note

1. All typical values are measured at  $T_{amb}$  = 25 °C.

### 74ALVC573

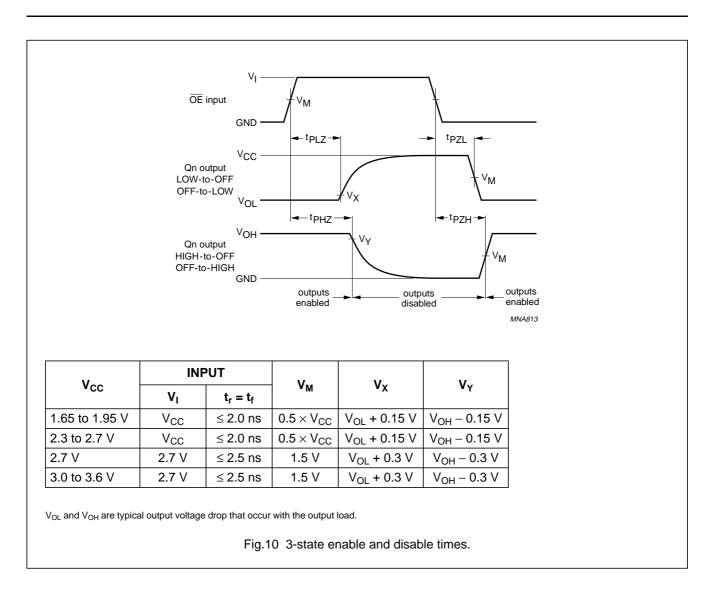
#### AC WAVEFORMS





N N	v	INPUT			
V <sub>cc</sub>	V <sub>M</sub>	VI	t <sub>r</sub> = t <sub>f</sub>		
1.65 to 1.95 V	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 2.0 ns		
2.3 to 2.7 V	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 2.0 ns		
2.7 V	1.5 V	2.7 V	≤ 2.5 ns		
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns		

Fig.9 Latch Enable (LE) input pulse width and latch enable input to output (Qn) propagation delays.



### 74ALVC573

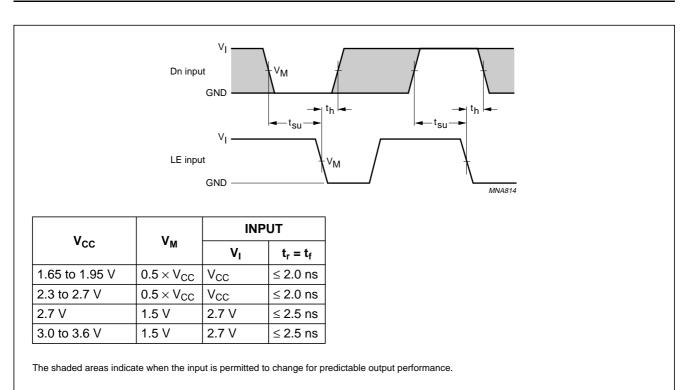
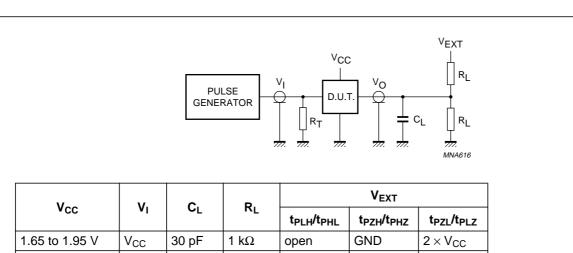


Fig.11 Data set-up and hold times for Dn input to LE input.



1.65 to 1.95 V	V <sub>CC</sub>	30 pF	1 kΩ	open	GND	$2 \times V_{CC}$
2.3 to 2.7 V	V <sub>CC</sub>	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V

Definitions for test circuit:

R<sub>L</sub> = Load resistor.

 $C_L$  = Load capacitance including jig and probe capacitance.

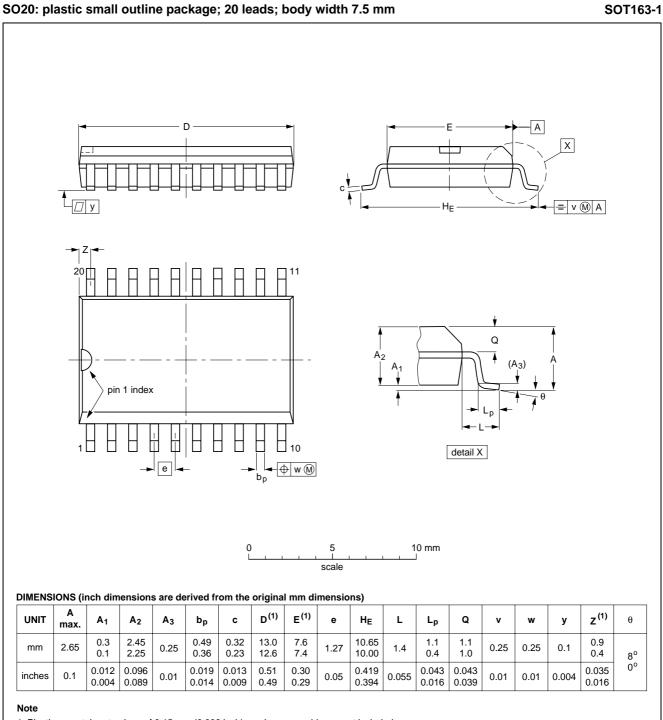
 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

Fig.12 Load circuitry for switching times.

74ALVC573

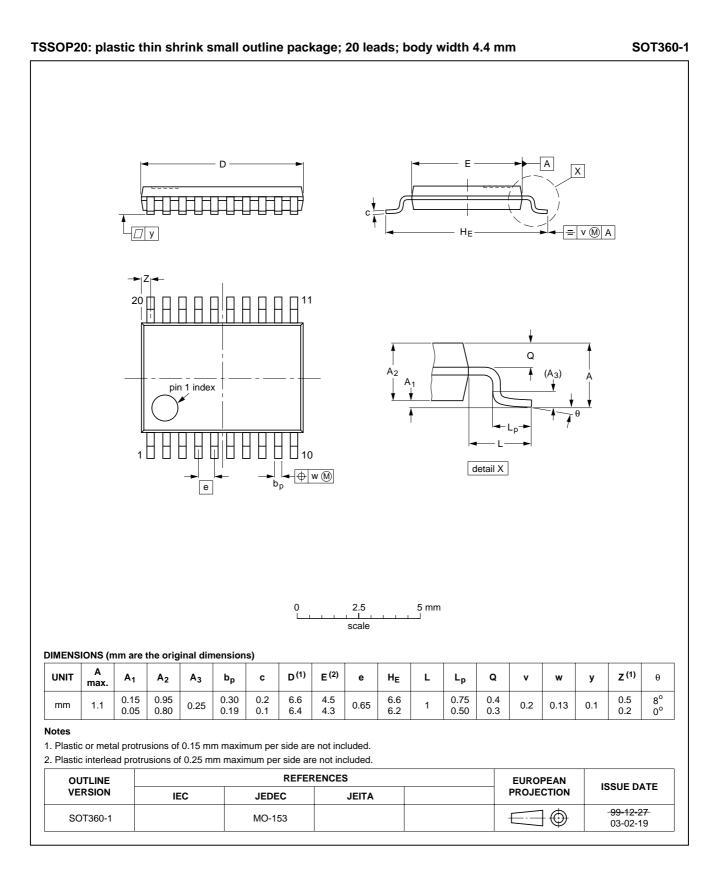
### Octal D-type transparent latch; 3-state

#### PACKAGE OUTLINES

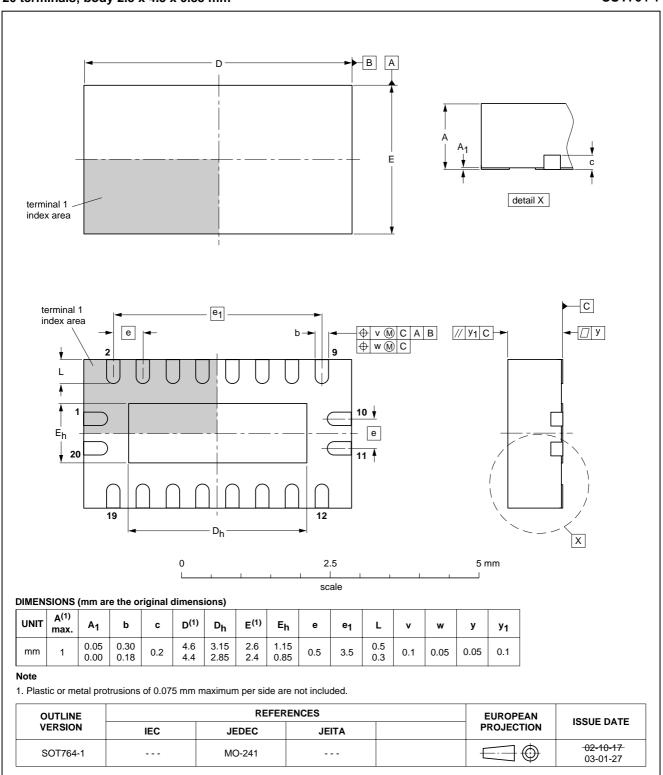


1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT163-1	075E04	MS-013				<del>-99-12-27</del> 03-02-19	



### 74ALVC573



#### DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

### 74ALVC573

#### SOLDERING

#### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

#### **Reflow soldering**

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 220 °C (SnPb process) or below 245 °C (Pb-free process)
  - for all BGA and SSOP-T packages
  - for packages with a thickness  $\geq$  2.5 mm
  - for packages with a thickness < 2.5 mm and a volume ≥ 350 mm<sup>3</sup> so called thick/large packages.
- below 235 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm<sup>3</sup> so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

#### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems. To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320  $^\circ\text{C}.$ 

### 74ALVC573

#### Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE <sup>(1)</sup>	SOLDERING METHOD	
	WAVE	REFLOW <sup>(2)</sup>
BGA, LBGA, LFBGA, SQFP, SSOP-T <sup>(3)</sup> , TFBGA, VFBGA	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable <sup>(4)</sup>	suitable
PLCC <sup>(5)</sup> , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended <sup>(5)(6)</sup>	suitable
SSOP, TSSOP, VSO, VSSOP	not recommended <sup>(7)</sup>	suitable

#### Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding 217 °C ± 10 °C measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.
- 4. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 5. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 6. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 7. Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

74ALVC573

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

#### Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

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